Noninverting Buffer / CMOS Logic Level Shifter

with LSTTL-Compatible Inputs

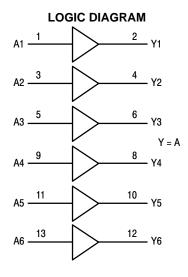
The MC74VHCT50A is a hex noninverting buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

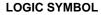
The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output.

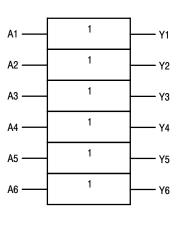
The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHCT50A input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHCT50A to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC}=0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: $t_{PD} = 3.5 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- CMOS–Compatible Outputs: $V_{OH} > 0.8 V_{CC}$; $V_{OL} < 0.1 V_{CC}$ @Load
- Power Down Protection Provided on Inputs and Outputs
- Pb-Free Packages are Available









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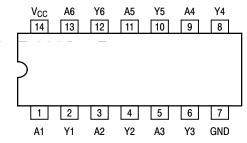


14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G



14-LEAD SOIC EIAJ M SUFFIX CASE 965

PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

FUNCTION TABLE

A Input	Y Output
L	L
Н	Н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	$-0.5 \le V_{I} \le +7.0$	V
V _{OUT}	DC Output Voltage Output in HIGH or LOW State (Note 1)	$-0.5 \le V_{O} \le +7.0$	V
I _{IK}	DC Input Diode Current	-20	mA
I _{OK}	DC Output Diode Current	±20	mA
I _O	DC Output Source/Sink Current	±25	mA
I _{CC}	DC Supply Current per Supply Pin	±50	mA
I _{GND}	DC Ground Current per Ground Pin	±50	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature under Bias	+ 150	°C
θ_{JA}	Thermal Resistance SOIC TSSOP	125 170	°C/W
P _D	Power Dissipation in Still Air SOIC TSSOP	500 450	mW
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 2000	V
I _{Latch-Up}	Latch–Up Performance Above V _{CC} and Below GND at 85°C (Note 5)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- I_O absolute maximum rating must be observed.
 Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

CI	naracteristics	Symbol	Min	Max	Unit
DC Supply Voltage		V _{CC}	2.0	5.5	V
DC Input Voltage		V _{IN}	0.0	5.5	V
DC Output Voltage	V _{CC} = 0 High or Low State	V _{OUT}	0.0 0.0	5.5 V _{CC}	V
Operating Temperature Ra	inge	T _A	- 55	+125	°C
Input Rise and Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	t _r , t _f	0 0	100 20	ns/V

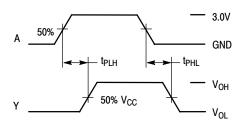
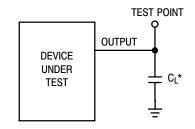


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	1	Γ _A = 25°0	С	T _A ≤	85°C	T _A ≤ '	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
V _{IL}	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μА
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μΑ
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OFF}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μА

AC ELECTRICAL CHARACTERISTICS ($C_{load} = 50 \text{ pF}$, Input $t_f = t_f = 3.0 \text{ns}$)

				1	Γ _A = 25°(C	_ T _A ≤	85°C	T _A ≤ 1	125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propogation Delay,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0			ns
	Input A to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.2 7.0	7.5 8.5		8.5 9.5		9.5 10.5	
C _{IN}	Maximum Input Capacitance				5	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 6)	15	pF

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}, \ C_L = 50 \text{pF}, \ V_{CC} = 5.0 \text{V})$

		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.8	1.0	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.8	-1.0	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

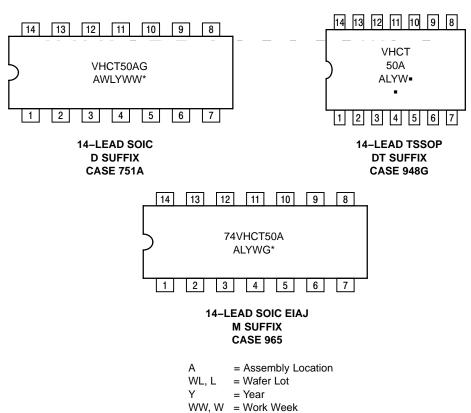
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT50AD	SOIC-14	55 Units / Rail
MC74VHCT50ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74VHCT50ADR2	SOIC-14	2500 / Tape & Reel
MC74VHCT50ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT50ADT	TSSOP-14	96 Units / Rail
MC74VHCT50ADTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74VHCT50ADTR2	TSSOP-14	2500 / Tape & Reel
MC74VHCT50ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT50AM	SOIC EIAJ	50 Units / Rail
MC74VHCT50AMG	SOIC EIAJ (Pb-Free)	50 Units / Rail
MC74VHCT50AMEL	SOIC EIAJ	2000 / Tape & Reel
MC74VHCT50AMELG	SOIC EIAJ (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS

(Top View)



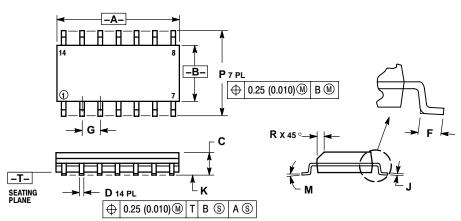
^{*}See Applications Note #AND8004/D for date code and traceability information.

G or ■ = Pb-Free Package

PACKAGE DIMENSIONS

D SUFFIX

PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE G

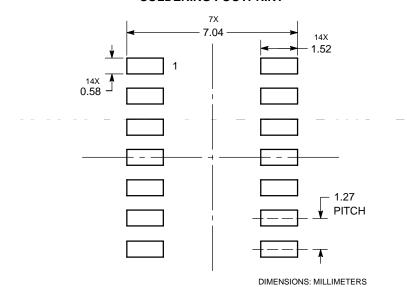


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE
 MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
 PER SIDE.
- PEH SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
۲	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

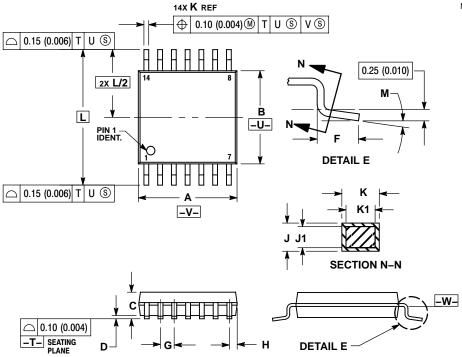
SOLDERING FOOTPRINT



PACKAGE DIMENSIONS

DT SUFFIX

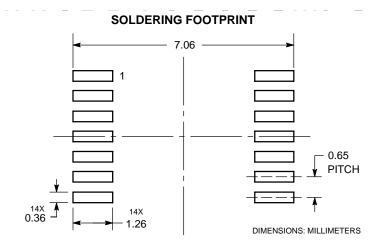
PLASTIC TSSOP PACKAGE CASE 948G-01 **ISSUE B**



NOTES:

- DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATIM DI ANE JAK.

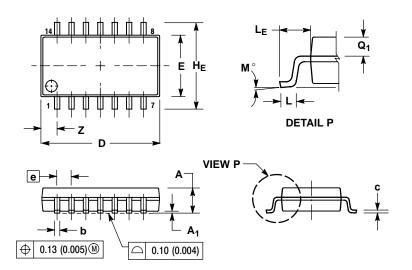
DETE	RMINE) AT DA	TUM PL	ANF -\A	
	MILLIN	IÉTERS	INC	HÈS	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0 °	8 °	0 °	8 °	



PACKAGE DIMENSIONS

M SUFFIX

PLASTIC SOIC EIAJ PACKAGE CASE 965-01 **ISSUE A**



NOTES:

- 1. DIMENSIO Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
- 2. CONTROLLING DIMENSION: MILLIMETER.
- MOLD FLASH OR PROTRUSION. MILLIMETER.

 DIMENSIONS D AND E DO NOT INCLUDE

 MOLD FLASH OR PROTRUSIONS AND ARE

 MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (U.U.D) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD

	•	,			
	MILLIN	ILLIMETERS INC		HES	
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
С	0.10	0.20	0.004	0.008	
D	9.90	10.50	0.390	0.413	
Ε	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050 BSC		
HE	7.40	8.20	0.291	0.323	
0.50	0.50	0.85	0.020	0.033	
LΕ	1.10	1.50	0.043	0.059	
M	0 °	10°	0 °	10°	
Q1	0.70	0.90	0.028	0.035	
Z		1.42		0.056	

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